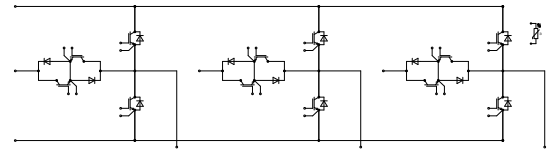
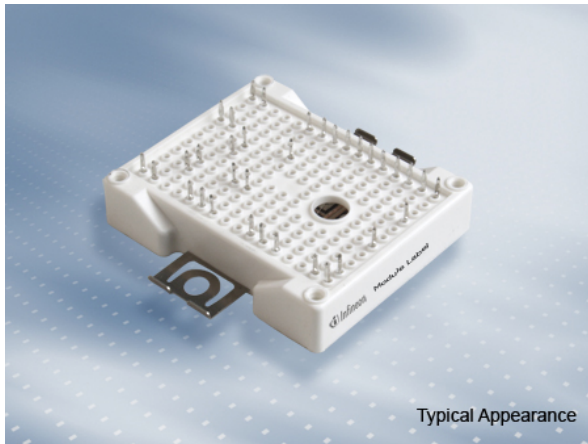


EasyPACK™ Modul mit schnellem Trench/Feldstopp IGBT4 und Emitter Controlled 4 Diode und PressFIT / NTC

EasyPACK™ module with fast Trench/Fieldstop IGBT4 and Emitter Controlled 4 diode and PressFIT / NTC

Vorläufige Daten / Preliminary Data



$V_{CES} = 1200V$

$I_{C\ nom} = 25A / I_{CRM} = 50A$

Potentielle Anwendungen

- 3-Level-Applikationen
- Solar Anwendungen

Elektrische Eigenschaften

- High Speed IGBT H3
- Niederinduktives Design
- Niedrige Schaltverluste

Mechanische Eigenschaften

- Al_2O_3 Substrat mit kleinem thermischen Widerstand
- Kompaktes Design
- PressFIT Verbindungstechnik
- Robuste Montage durch integrierte Befestigungsklammern

Potential Applications

- 3-level-applications
- Solar applications

Electrical Features

- High speed IGBT H3
- Low inductive design
- Low switching losses

Mechanical Features

- Al_2O_3 substrate with low thermal resistance
- Compact design
- PressFIT contact technology
- Rugged mounting due to integrated mounting clamps

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, T1 / T4 / IGBT, T1 / T4

Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
Kollektor-Dauergleichstrom Continuous DC collector current	$T_H = 60^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	I_{CDC}	25	A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	50	A
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

			min.	typ.	max.		
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 25\text{ A}$ $V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$	2,05 2,50 2,60	2,40	V V V	
Gate-Schwellenspannung Gate threshold voltage	$I_C = 0,85\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,25	5,80	6,35	V
Gateladung Gate charge	$V_{GE} = -15 / 15\text{ V}$		Q_G	0,13			μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	0,0			Ω
Eingangskapazität Input capacitance	$f = 1000\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	1,43			nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 1000\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,075			nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	I_{CES}			1,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}			100	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 25\text{ A}, V_{CE} = 350\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 20\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,055 0,055 0,055			μs μs μs
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 25\text{ A}, V_{CE} = 350\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 20\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,04 0,04 0,04			μs μs μs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 25\text{ A}, V_{CE} = 350\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 20\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,185 0,23 0,24			μs μs μs
Fallzeit, induktive Last Fall time, inductive load	$I_C = 25\text{ A}, V_{CE} = 350\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 20\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,025 0,05 0,055			μs μs μs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 25\text{ A}, V_{CE} = 350\text{ V}, L\sigma = 30\text{ nH}$ $di/dt = 1050\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Gon} = 20\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	0,67 1,00 1,05			mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 25\text{ A}, V_{CE} = 350\text{ V}, L\sigma = 30\text{ nH}$ $du/dt = 3000\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Goff} = 20\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	0,60 0,95 1,00			mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$	$t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	I_{SC}	80			A
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro IGBT / per IGBT		R_{thJH}	1,45			K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150		$^{\circ}\text{C}$